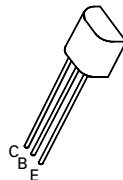


PNP SILICON PLANAR MEDIUM POWER TRANSISTOR

ISSUE 2 – MARCH 94

ZTX537C



**E-Line
TO92 Compatible**

ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-1	A
Continuous Collector Current	I_C	-800	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	750	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +175	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-50			V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-45			V	$I_C = -100\mu A$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -100\mu A, I_C = 0$
Collector Cut-Off Current	I_{CBO}			-100	nA	$V_{CB} = -45V$
Emitter Cut-Off Current	I_{EBO}			-0.2	μA	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.7	V	$I_C = -500mA, I_B = -50mA^*$
Base-Emitter Saturation Voltage	$V_{BE(on)}$			-1.2	V	$I_C = -300mA, V_{CE} = -1V^*$
Static Forward Current Transfer Ratio	h_{FE}	250 170		630		$I_C = -100mA, V_{CE} = -1V^*$ $I_C = -300mA, V_{CE} = -1V^*$
Transition Frequency	f_T		200		MHz	$I_C = -10mA, V_{CE} = -5V$ $f = 50MHz$
Output Capacitance	C_{obo}		12		pF	$V_{CB} = -10V, f = 1MHz$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$